

IN THE SPECIFICATION:

Please place the following amended abstract after page 17 of the filed application:

ABSTRACT

The invention relates to a semiconductor laser consisting of an active waveguide (3) comprising an active region surrounded by a filling material (5) and which is coupled to a distributed reflector (7, 8). Said distributed reflector (7, 8) is made from the aforementioned filling material (5) and is disposed along the length of the lateral sides of the active region (4) essentially parallel to same and in the form of a structuring having a photonic band gap along the longitudinal axis (X) of the laser. According to the invention, the structuring defines a first photonic crystal with columns (9) forming diffracting elements, said crystal comprising a mesh having dimensions of the order of the wavelength of photons in the guided mode which circulate in the active waveguide (3).